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NPN - MJ15022, MJ15024*

*MJ15024 is a Preferred Device

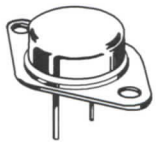
Silicon Power Transistors

The MJ15022 and MJ15024 are PowerBase power transistors designed for high power audio, disk head positioners and other linear applications.

Features

- High Safe Operating Area (100% Tested) – 2 A @ 80 V
- High DC Current Gain – h_{FE} = 15 (Min) @ I_C = 8 Adc

16 AMPERES
SILICON POWER TRANSISTORS
200 – 250 VOLTS, 250 WATTS



(TO–3)

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage MJ15022 MJ15024	V_{CEO}	 200 250	Vdc
Collector–Base Voltage MJ15022 MJ15024	V_{CBO}	 350 400	Vdc
Emitter–Base Voltage	V_{EBO}	5	Vdc
Collector–Emitter Voltage	V_{CEX}	400	Vdc
Collector Current – Continuous – Peak (Note 1)	I_C	16 30	Adc
Base Current – Continuous	I_B	5	Adc
Total Device Dissipation @ T_C = 25°C Derate above 25°C	P_D	250 1.43	W W/°C
Operating and Storage Junction Temperature Range	T_J, T_{stg}	–65 to +200	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max	Unit
Thermal Resistance, Junction–to–Case	$R_{\theta JC}$	0.70	°C/W

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle ≤ 10%.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Sustaining Voltage (Note 2) (I_C = 100 mAdc, I_B = 0)	MJ15022 MJ15024	$V_{CEO(sus)}$	 200 250	 – –	–
Collector Cutoff Current (V_{CE} = 200 Vdc, $V_{BE(off)}$ = 1.5 Vdc) (V_{CE} = 250 Vdc, $V_{BE(off)}$ = 1.5 Vdc)	MJ15022 MJ15024	I_{CEX}	 – –	 250 250	μAdc
Collector Cutoff Current (V_{CE} = 150 Vdc, I_B = 0) (V_{CE} = 200 vdc, I_B = 0)	MJ15022 MJ15024	I_{CEO}	 – –	 500 500	μAdc
Emitter Cutoff Current (V_{CE} = 5 Vdc, I_B = 0)		I_{EBO}	–	500	μAdc
SECOND BREAKDOWN					
Second Breakdown Collector Current with Base Forward Biased (V_{CE} = 50 Vdc, t = 0.5 s (non–repetitive)) (V_{CE} = 80 Vdc, t = 0.5 s (non–repetitive))		$I_{S/b}$	 5 2	 – –	Adc
ON CHARACTERISTICS					
DC Current Gain (I_C = 8 Adc, V_{CE} = 4 Vdc) (I_C = 16 Adc, V_{CE} = 4 Vdc)		h_{FE}	 15 5	 60 –	–
Collector–Emitter Saturation Voltage (I_C = 8 Adc, I_B = 0.8 Adc) (I_C = 16 Adc, I_B = 3.2 Adc)		$V_{CE(sat)}$	 – –	 1.4 4.0	Vdc
Base–Emitter On Voltage (I_C = 8 Adc, V_{CE} = 4 Vdc)		$V_{BE(on)}$	–	2.2	Vdc
DYNAMIC CHARACTERISTICS					
Current–Gain – Bandwidth Product (I_C = 1 Adc, V_{CE} = 10 Vdc, f_{test} = 1 MHz)		f_T	4	–	MHz
Output Capacitance (V_{CB} = 10 Vdc, I_E = 0, f_{test} = 1 MHz)		C_{ob}	–	500	pF

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2%.

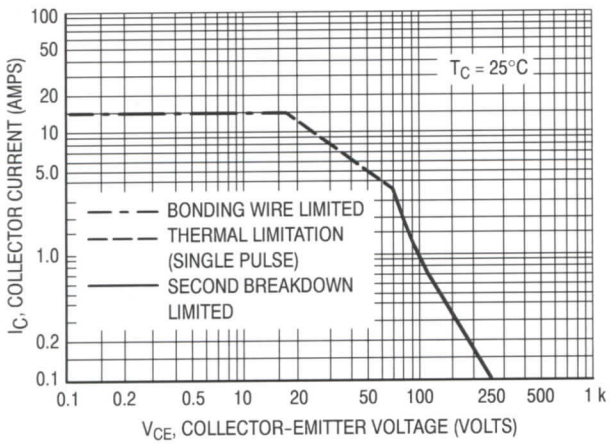


Figure 1. Active–Region Safe Operating Area

There are two limitations on the powerhandling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 1 is based on $T_{J(pk)}$ = 200°C; T_C is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values Ion than the limitations imposed by second breakdown.